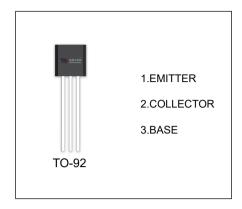


2SB561 TRANSISTOR (PNP)

FEATURES

Low Frequency Power Amplifier



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SB561	TO-92	Bul	1000pcs/Bag
2SB561-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-25	V
V _{CEO}	Collector-Emitter Voltage	-20	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current -Continuous	-0.7	А
P _D	Collector Power Dissipation	500	mW
R _{0 JA}	Thermal Resistance rom Junction o Ambient	250	°C /W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C



Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =- 0.01mA,I _E =0	-25			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA,I _B =0	-20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-0.01mA,I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-20V,I _E =0			-1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V,I _C =0			-1	μA
DC current gain	h _{FE} *	V _{CE} =-1V, I _C =-0.15A	85		240	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-0.5A,I _B =-0.05A			-0.5	V
Base-emitter voltage	V _{BE}	V _{CE} =-1V, I _C =-0.15A			-1	V
Collector output capacitance	C _{ob}	V _{CB} =-10V,I _E =0, f=1MHz		20		pF
Transition frequency	f _T	V _{CE} =-1V, I _C =-0.15A		350		MHz

^{*}Pulse test

CLASSIFICATION OF h_{FE}

RANK	В	С
RANGE	85-170	120-240